

CLAIMS

What is claimed is:

- 1 1. A method of forming a semiconductor substrate, comprising:
2 etching a groove into a bulk silicon substrate;
3 forming a dielectric in said groove and planarizing said silicon
4 substrate to form at least one patterned dielectric island in said silicon
5 substrate;
6 forming an amorphous silicon layer on exposed portions of said
7 silicon substrate and said at least one dielectric island;
8 crystallizing said amorphous silicon layer using the exposed silicon
9 substrate as a seed, said silicon substrate having direct contact with the
10 formed silicon layer serving as a crystal growth seeding for the crystallization
11 process, and converting the silicon layer to crystallized silicon; and
12 performing a shallow trench isolation (STI) process, to form oxide
13 isolations between devices.
- 1 2. The method according to claim 1, wherein defects in a defect zone in said
2 substrate are removed by replacing said defects with dielectric in said STI
3 process.
- 1 3. The method according to claim 2, wherein circuits are arranged such that

2 original defect zones in said substrate are used as an isolation area.

1 4. The method according to claim 2, wherein said performing said STI
2 process includes using a mask, and

3 wherein said mask used for said STI process is designed such that
4 original defect zones in said substrate are converted to isolations.

1 5. The method according to claim 1, wherein said amorphous silicon layer
2 comprises polycrystalline silicon or microcrystalline silicon and rendered
3 amorphous by an inert ion implantation.

1 6. The method according to claim 1, wherein said crystallizing comprises
2 crystallizing through an annealing process.

1 7. The method according to claim 6, wherein said annealing process
2 comprises a laser beam annealing process.

1 8. The method according to claim 6, wherein said annealing process
2 comprises an ion beam annealing process.

1 9. The method according to claim 1, wherein said crystallized layer has a
2 crystal orientation and structure which follow those of the underlying
3 substrate.

1 10. A method of forming a substrate for mixed logic and memory
2 applications, comprising:
3 forming a buried oxide layer on a single crystal silicon substrate;
4 performing a silicon epitaxial lateral overgrowth process using an
5 exposed area of the silicon substrate as the crystallization seeding, to form a
6 single crystal silicon on top of said buried oxide layer by lateral overgrowth
7 from the exposed area of the silicon substrate; and
8 forming shallow trench isolations (STIs) at locations to remove
9 imperfect silicon on said oxide layer.

1 11. A method of forming a substrate for mixed logic and memory
2 applications, comprising:
3 forming a buried oxide layer on a single crystal silicon substrate;
4 forming an amorphous silicon layer over the oxide layer and silicon
5 substrate;
6 annealing said amorphous silicon layer and converting said
7 amorphous layer to a single crystalline silicon; and
8 forming shallow trench isolations (STIs) at locations to remove
9 imperfect silicon on said oxide layer.

1 12. The method according to claim 11, wherein said substrate has a mixed
2 bulk region and a silicon-on-insulator (SOI) region, said method further

3 comprising:

4 fabricating a logic device in the silicon-on-insulator (SOI) region.

1 13. The method according to claim 12, wherein said bulk region includes at
2 least one of a memory array, a dynamic random access memory (DRAM), a
3 static random access memory (SRAM), a flash memory, a predetermined high
4 voltage, high power circuit, and an analog circuit.

1 14. The method according to claim 11, wherein said substrate has a mixed
2 bulk region and a silicon-on-insulator (SOI) region, said method further
3 comprising:
4 fabricating a memory device in the bulk silicon region.

1 15. The method according to claim 14, wherein said SOI region includes at
2 least one of logic circuit, a predetermined low voltage, low power circuit, and
3 a high performance digital circuit operating at a predetermined clock rate.

1 16. The method according to claim 11, wherein said forming said buried
2 oxide layer comprises forming a groove in the silicon substrate, and filling
3 said groove with oxide.

1 17. The method according to claim 11, wherein logic devices are placed in
2 strips of silicon-on-insulator (SOI) islands which are isolated by regions

3 formed by the shallow trench isolation (STI) process.

1 18. The method according to claim 11, wherein noise-sensitive circuits are
2 placed in strips of silicon-on-insulator (SOI) islands which are isolated by
3 regions formed by the shallow trench isolation (STI) process.

1 19. The method according to claim 17, wherein said logic devices comprise
2 P-FET and N-FET devices.

1 20. The method according to claim 11, wherein said substrate includes a bulk
2 region, and
3 wherein thermal-sensitive circuits are placed in the bulk region such
4 that temperature control is maximized.

1 21. A method of forming a substrate for mixed memory and logic
2 applications, comprising:
3 forming a dielectric on a substrate;
4 performing an epitaxial lateral overgrowth process over the dielectric;
5 performing a pattern isolation operation, to form an isolation while
6 removing a defective area; and
7 forming a thermal oxide to consume the silicon in an exposed area,
8 such that a first remaining area forms a silicon-on-insulator (SOI) structure,
9 and a second remaining area forms a bulk structure.

1 22. The method according to claim 21, wherein said dielectric has a thickness
2 in a range of about 500 Å to about 3000 Å, and is patterned through a dry
3 etch, and
4 wherein a corner of the patterned dielectric is rounded.

1 23. A method of forming a structure for mixed memory and logic
2 applications, comprising:
3 processing a buried dielectric layer on a single crystal silicon substrate
4 by depositing a dielectric and patterning said dielectric in said silicon
5 substrate;
6 forming an amorphous silicon layer over the dielectric layer and the
7 silicon substrate surface;
8 converting said amorphous silicon layer to a single crystalline silicon
9 by an annealing process;
10 patterning said silicon surface with a nitride mask; and
11 oxidizing exposed silicon surfaces including locations to remove
12 imperfect silicon on insulator layers.

1 24. A semiconductor device, comprising:
2 a bulk silicon substrate;
3 at least one patterned oxide island formed in said silicon substrate,
4 said at least one island formed of a shallow groove filled with an oxide;

5 an amorphous silicon layer formed on exposed portions of said silicon
6 substrate and said at least one oxide island, said amorphous silicon layer
7 being crystallized using the exposed silicon substrate as a seed, said silicon
8 substrate having direct contact with the formed silicon layer serving as a
9 crystal growth seeding for the crystallization process, and converting the
10 silicon layer to crystallized silicon; and

11 shallow trench isolations formed respectively between adjacent
12 devices on said semiconductor device, wherein a portion of the silicon layer
13 above the islands is etched to form a cavity, and a same material as said
14 islands is formed in the cavity,

15 an upper surface of said trench isolations, said substrate, and said
16 silicon layer being planarized.

1 25. A substrate for mixed logic and memory applications, comprising:

2 a single crystal silicon substrate forming a bulk silicon region;

3 a buried oxide layer on the single crystal silicon substrate forming a
4 silicon-on-insulator (SOI) region;

5 an amorphous silicon layer formed substantially over the oxide layer;

6 and

7 shallow trench isolations (STIs) formed at predetermined locations to
8 remove defects on the SOI region.

1 26. The substrate according to claim 25, further comprising a logic device

2 formed in the silicon-on-insulator (SOI) region.

1 27. The substrate according to claim 25, further comprising a memory
2 device positioned in the bulk silicon region.

1 28. A semiconductor device, comprising:
2 a bulk silicon substrate;
3 at least one patterned oxide island formed in said silicon substrate,
4 said at least one island formed of a shallow groove filled with an oxide;
5 a SiGe layer formed on exposed portions of said silicon substrate and
6 said at least one oxide island, said SiGe layer being crystallized using the
7 exposed silicon substrate as a seed, said silicon substrate having direct
8 contact with the formed SiGe layer serving as a crystal growth seeding for the
9 crystallization process, and converting the SiGe layer to crystallized silicon;
10 and
11 shallow trench isolations formed respectively between adjacent
12 devices on said substrate, wherein a portion of the SiGe layer above the
13 islands is etched to form a cavity, and a same material as said islands is
14 formed in the cavity, an upper surface of said trench isolations, said substrate,
15 and said SiGe layer being planarized,
16 wherein said SiGe layer is at least partially positioned on a bulk
17 region of said substrate and a silicon-on-insulator (SOI) portion of said
18 substrate.